

描述 / Descriptions

DFN 2×2B-6L 塑封封装 P 沟道 MOS 场效应管。

P-Channel Enhancement Mode Field Effect Transistor in a DFN 2×2B-6L Plastic Package.

特征 / Features

$V_{DS}(V) = -20V$

$I_D = -11A$

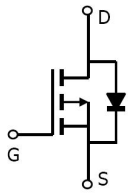
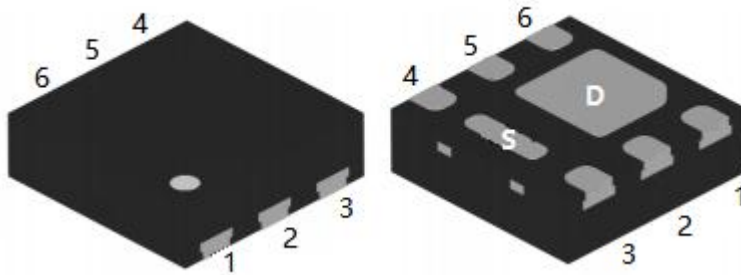
$R_{DS(ON)}@-4.5V \leq 17m\Omega$ (Type. 15m Ω)

无卤产品。HF Product.

用途 / Applications

用于电源管理，便携式设备和电池供电系统。

Power Management in Notebook computer, Portable Equipment and Battery powered systems.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

出脚	定义
Pin1	D
Pin2	D
Pin3	G
Pin4	S
Pin5	D
Pin6	D

印章代码 / Marking

见印章说明 See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter		符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V_{GSS}	± 12	V
Continuous Drain Current		$I_D (T_a=25^\circ\text{C})$	-11	A
Pulsed Drain Current		I_{DM}	-44	A
Avalanche Current		I_{AS}	13	A
Avalanche energy L=0.5mH		E_{AS}	59	mJ
Power Dissipation for Single Operation		$P_D (T_a=25^\circ\text{C})$	3.0	W
Maximum Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-55 ~ 150	$^\circ\text{C}$
Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	$R_{\theta JA}$	40	$^\circ\text{C/W}$
	Steady State		75	$^\circ\text{C/W}$

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=-250\mu A$ $V_{GS}=0V$	-20	-23		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V$ $V_{GS}=0V$			-1.0	μA
Gate-Body leakage current	I_{GSS}	$V_{DS}=0V$ $V_{GS}=\pm 12V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=-250\mu A$	-0.4	-0.7	-1.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V$ $I_D=-10A$		15	17	m Ω
		$V_{GS}=-2.5V$ $I_D=-5A$		19	25	
		$V_{GS}=-1.8V$ $I_D=-1A$		27	38	
Diode Forward Voltage	V_{SD}	$I_S=-1A$ $V_{GS}=0V$			-1.2	V
Total Gate Charge	Q_g	$V_{GS}=-4.5V$ $V_{DS}=-6V$ $I_D=-8A$		12.7		nC
Gate-Source Charge	Q_{gs}			1.7		
Gate-Drain Charge	Q_{gd}			3.4		
Gate resistance	R_g	$V_{GS}=0V$, $V_{DS}=0V$, $f=1MHz$		13.5		
Input Capacitance	C_{iss}	$V_{GS}=0V$ $V_{DS}=-20V$ $f=1MHz$		2550		pF
Output Capacitance	C_{oss}			205		
Reverse Transfer Capacitance	C_{rss}			190		
Turn-on Delay Time	$t_{d(ON)}$	$V_{GS}=-4.5V$ $V_{DS}=-6V$ $R_L=0.75\Omega$ $R_{GEN}=3\Omega$		11		ns
Turn-on Rise Time	t_r			25		
Turn-off Delay Time	$t_{d(OFF)}$			70		
Turn-off Fall Time	t_f			41.5		

电参数曲线图 / Electrical Characteristic Curve

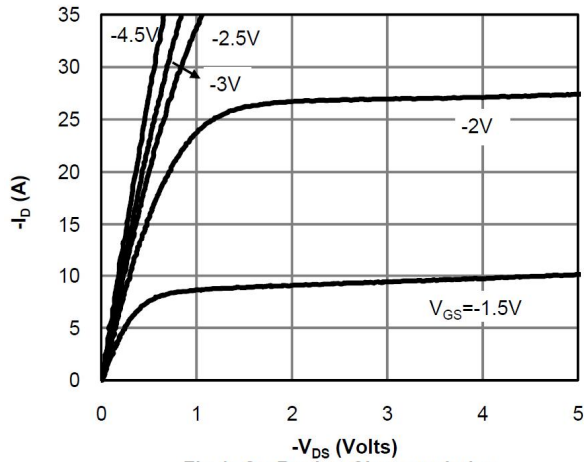


Fig 1: On-Region Characteristics

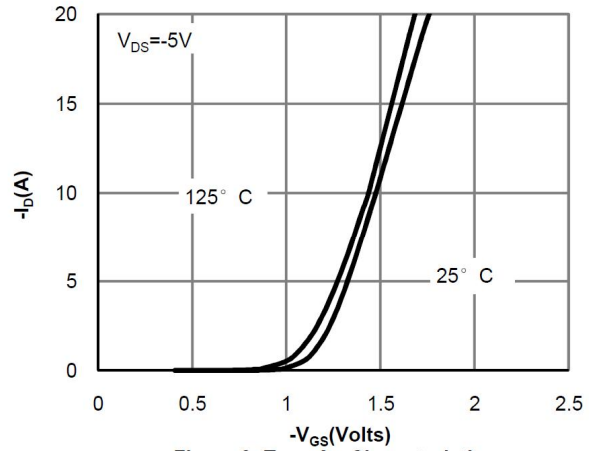


Figure 2: Transfer Characteristics

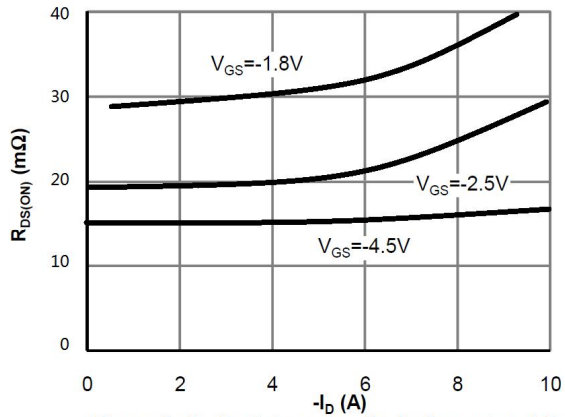


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

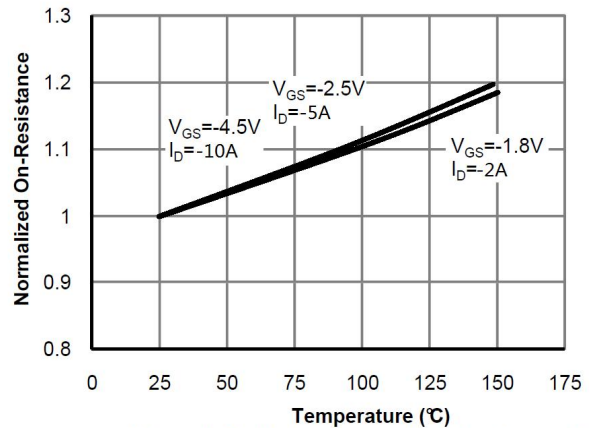


Figure 4: On-Resistance vs. Junction Temperature

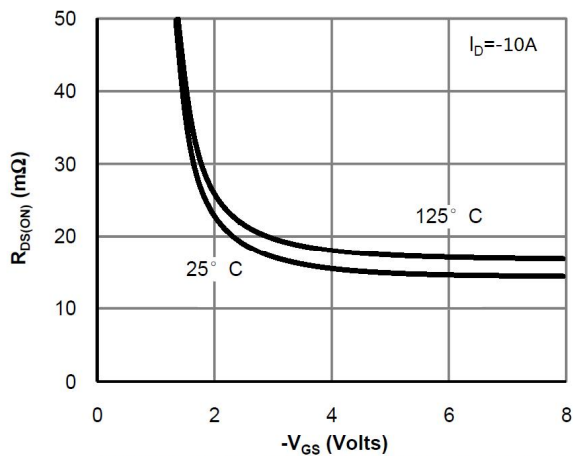


Figure 5: On-Resistance vs. Gate-Source Voltage

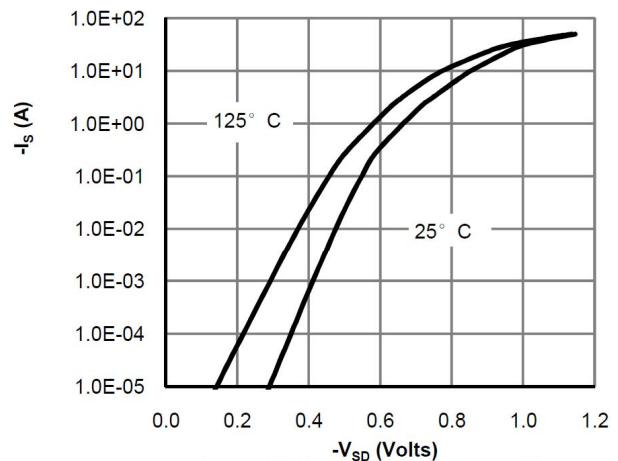
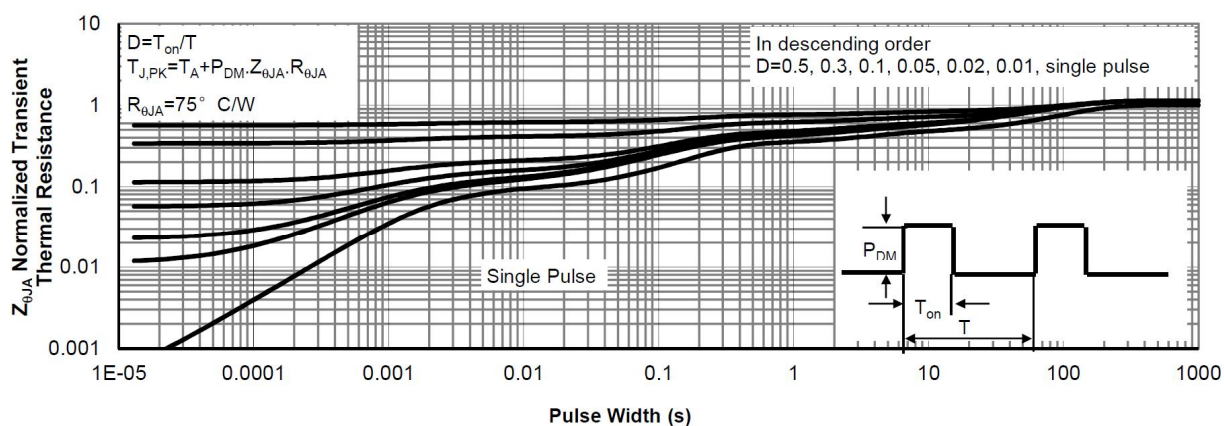
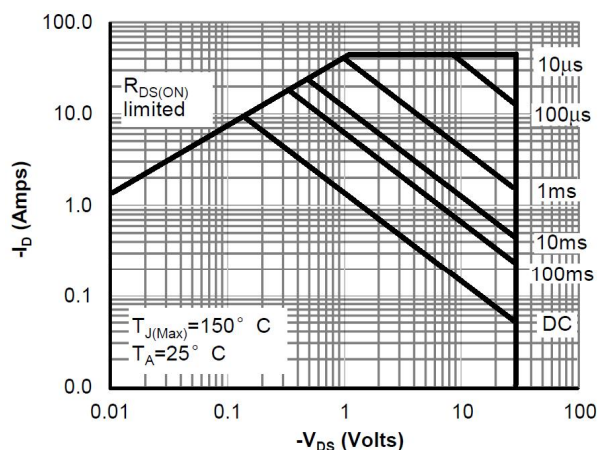
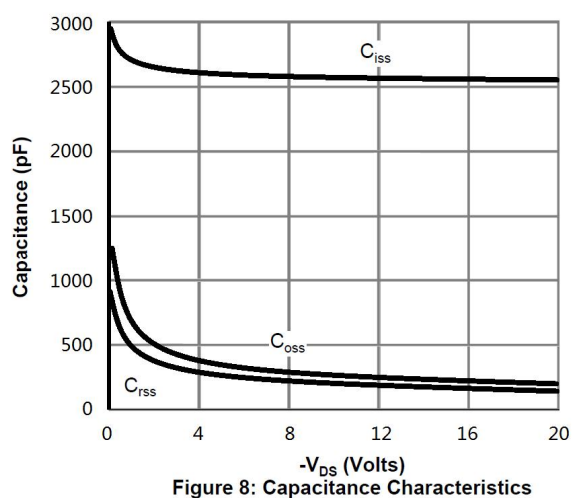
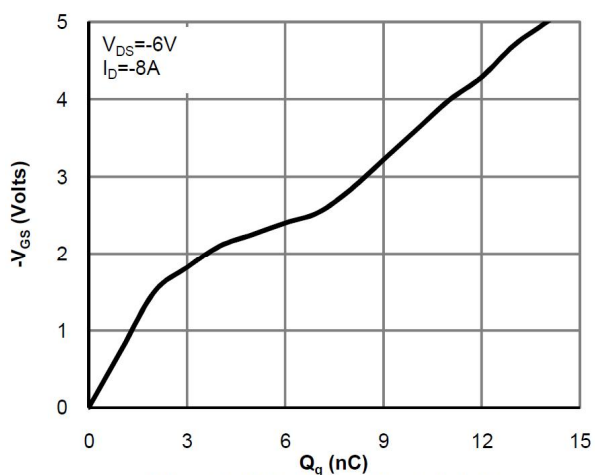


Figure 6: Body-Diode Characteristics

电参数曲线图 / Electrical Characteristic Curve

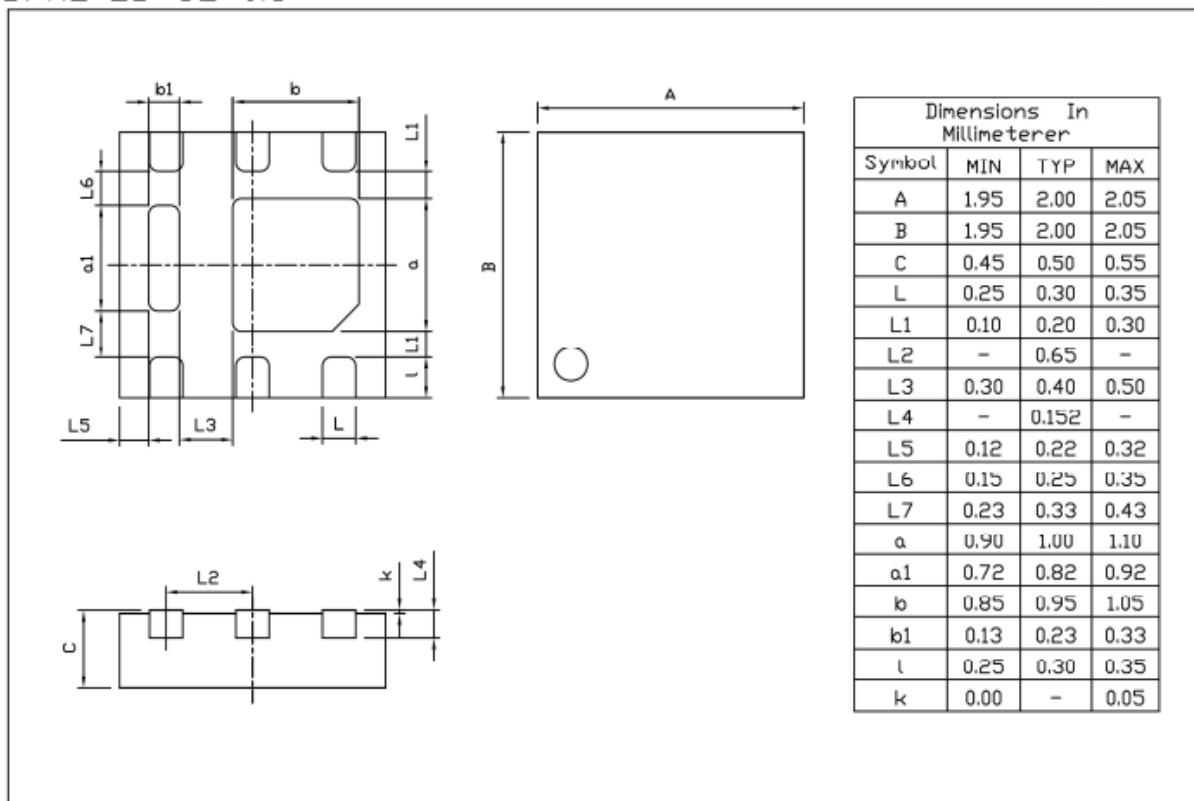




外形尺寸图 / Package Dimensions

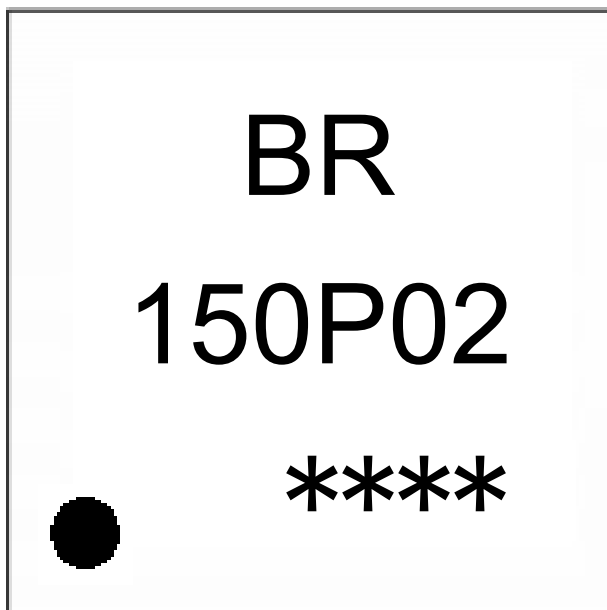
DFN2×2B-6L-0.5

Unit:mm



Rev.01 202006

印章说明 / Marking Instructions



说明：

BR： 为公司代码

150P02： 为型号代码

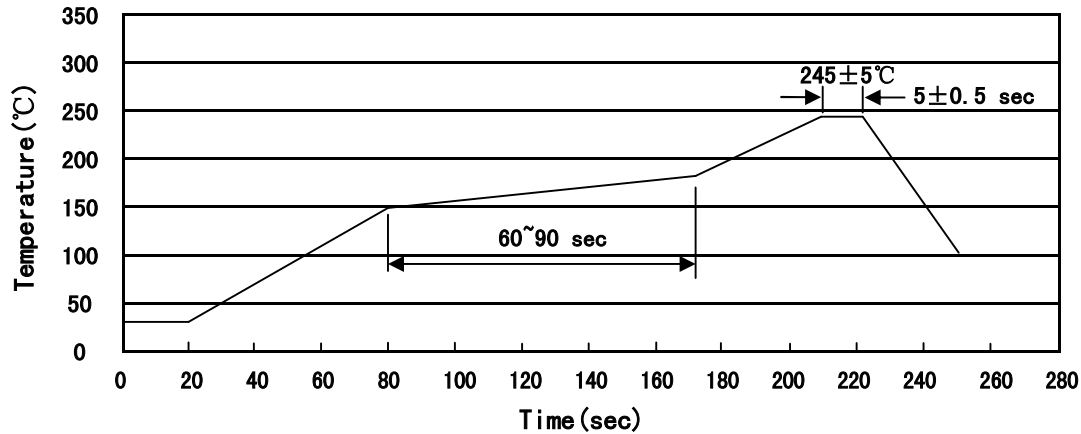
*****： 为生产批号代码，随生产批号变化

Note:

BR: Company Code

150P02: Product Type

*****: Lot No. Code, code change with Lot No

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)


说明：

- 1、预热温度 150 ~ 180°C，时间 60 ~ 90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
DFN 2 × 2B-6L	4,000	10	40,000	4	160,000	7" × 8	210×205×205	445×230×435

使用说明 / Notices